

DATA SHEET

TZA3033 **SDH/SONET STM1/OC3** **transimpedance amplifier**

Product specification
Supersedes data of 1998 Jul 08
File under Integrated Circuits, IC19

2000 Sep 29

SDH/SONET STM1/OC3 transimpedance amplifier

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FEATURES

- Low equivalent input noise of 1 pA/√Hz (typical)
- Wide dynamic range from 0.25 μA to 1.6 mA (typical)
- Differential transimpedance of 44 kΩ
- Bandwidth typical 130 MHz
- Differential outputs
- On-chip Automatic Gain Control (AGC)
- No external components required
- Single supply voltage from 3.0 to 5.5 V
- Bias voltage for PIN diode
- Pin compatible with SA5223.

APPLICATIONS

- Digital fibre optic receiver in short, medium and long haul optical telecommunications transmission systems or in high speed data networks
- Wideband RF gain block.

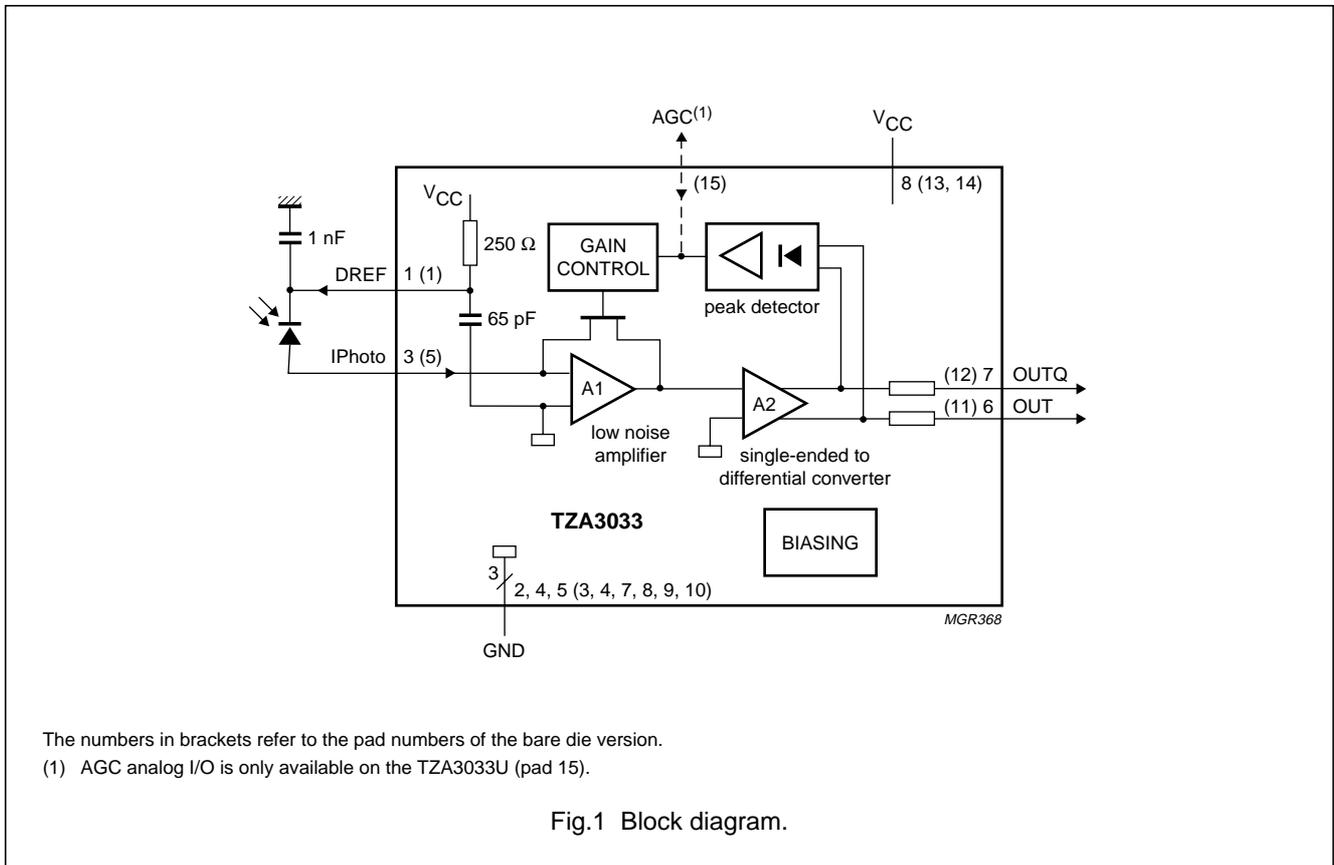
GENERAL DESCRIPTION

The TZA3033 is a low-noise transimpedance amplifier with AGC designed to be used in STM1/OC3 fibre optic links. It amplifies the current generated by a photo detector (PIN diode or avalanche photodiode) and converts it to a differential output voltage.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
TZA3033T	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1
TZA3033U	–	bare die in wafer pack carriers; die dimensions 1.030 × 1.300 mm	–

BLOCK DIAGRAM

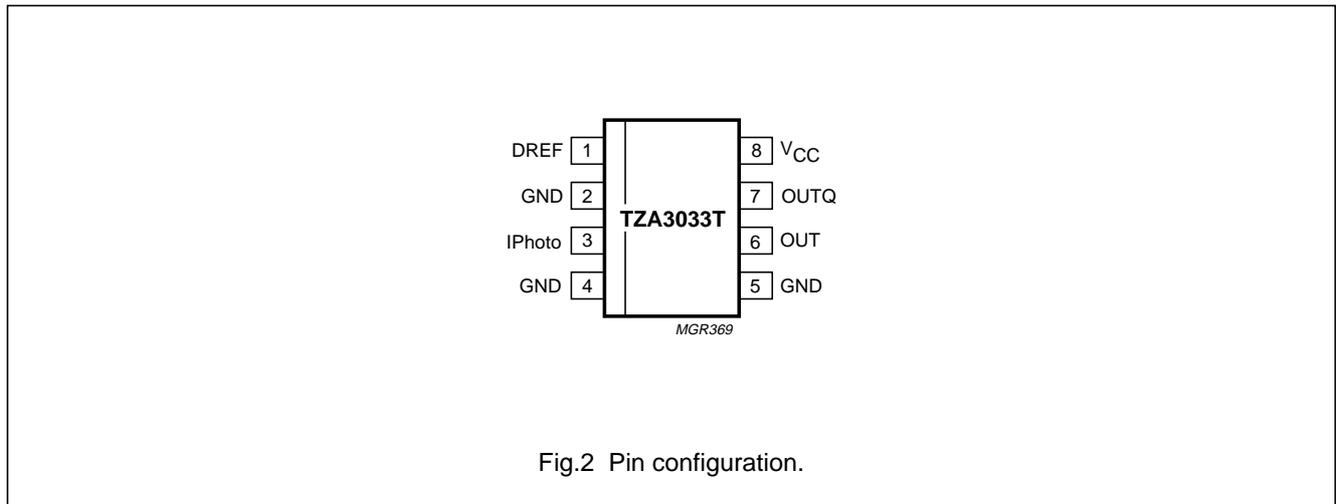


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PINNING

SYMBOL	PIN TZA3033T	PAD TZA3033U	TYPE	DESCRIPTION
DREF	1	1	analog output	bias voltage for PIN diode; cathode should be connected to this pin
TESTA	–	2	–	for test purposes only; to be left open in application
GND	2	3, 4	ground	ground
IPhoto	3	5	analog input	current input; anode of PIN diode should be connected to this pin; DC bias voltage is 1048 mV
TESTB	–	6	–	for test purposes only; to be left open in application
GND	4	7, 8	ground	ground
GND	5	9, 10	ground	ground
OUT	6	11	output	data output; pin OUT goes HIGH when current flows into pin IPhoto
OUTQ	7	12	output	data output; compliment of pin OUT
V _{CC}	8	13, 14	supply	supply voltage
AGC	–	15	input/output	AGC analog I/O



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FUNCTIONAL DESCRIPTION

The TZA3033 is a transimpedance amplifier intended for use in fibre optic links for signal recovery in STM1/OC3 applications. It amplifies the current generated by a photo detector (PIN diode or avalanche photodiode) and transforms it into a differential output voltage. The most important characteristics of the TZA3033 are high receiver sensitivity and wide dynamic range.

High receiver sensitivity is achieved by minimizing noise in the transimpedance amplifier. The signal current generated by a PIN diode can vary between 0.25 μ A to 1.6 mA (p-p). An AGC loop (see Fig.1) is implemented to make it possible to handle such a wide dynamic range. The AGC loop increases the dynamic range of the receiver by reducing the feedback resistance of the preamplifier.

The AGC loop hold capacitor is integrated on-chip, so an external capacitor is not needed for AGC. The AGC voltage can be monitored at pad 15 on the bare die (TZA3033U). Pad 15 is not bonded in the packaged device (TZA3033T). This pad can be left unconnected during normal operation. It can also be used to force an external AGC voltage. If pad 15 (AGC) is connected to V_{CC} , the internal AGC loop is disabled and the receiver gain is at a maximum. The maximum input current is then approximately 10 μ A.

A differential amplifier converts the output of the preamplifier to a differential voltage (see Fig.3).

The logic level symbol definitions are shown in Fig.4.

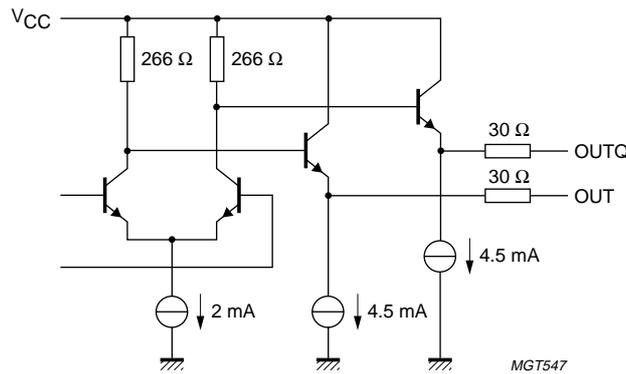


Fig.3 Data output circuit.

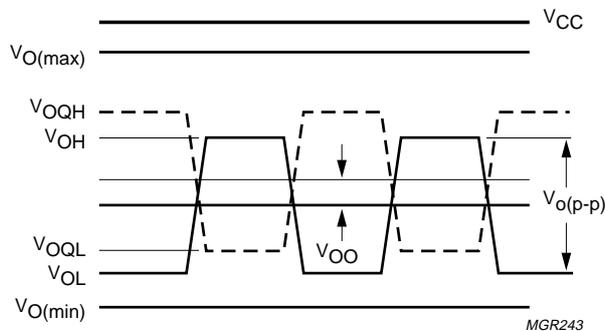


Fig.4 Logic level symbol definitions for data outputs OUT and OUTQ.

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PIN diode bias voltage DREF

The transimpedance amplifier together with the PIN diode determine to a large extent the performance of an optical receiver. The key parameters of a transimpedance amplifier like sensitivity, bandwidth, and the Power Supply Rejection Ratio (PSSR), are especially influenced by how the PIN diode is connected to the input and the layout around the input pin. The total capacitance at the input pin is critical to obtain the highest sensitivity. It should be kept to a minimum by reducing the capacitor of the PIN diode and the parasitics around the input pin. The PIN diode should be placed very close to the IC to reduce the parasitics. Because the capacitance of the PIN diode depends on the reverse voltage across it, the reverse voltage should be selected as high as possible.

The PIN diode can be connected to the input as shown in Fig.5. In Fig.5 the PIN diode is connected between DREF and IPhoto. Pin DREF provides an easy bias voltage for the PIN diode. The voltage at DREF is derived from V_{CC} by a low-pass filter. The low-pass filter consisting of the internal resistor R1, the internal capacitor C1 and the external capacitor C2 rejects the supply voltage noise. The external capacitor C2 should be equal to or larger than 1 nF for a high PSRR.

It is preferable to connect the cathode of the PIN diode to a voltage higher than V_{CC} when such a voltage source is available on the board. In this case the DREF pin can be left unconnected.

The reverse voltage across the PIN diode is 3.95 V (5 – 1.05 V) for a 5 V supply and 2.25 V (3.3 – 1.05 V) for a 3.3 V supply.

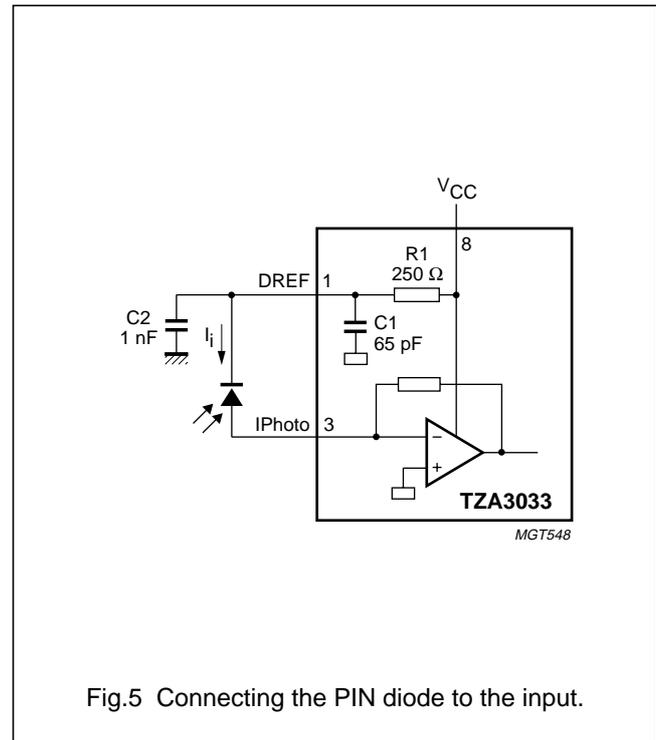


Fig.5 Connecting the PIN diode to the input.

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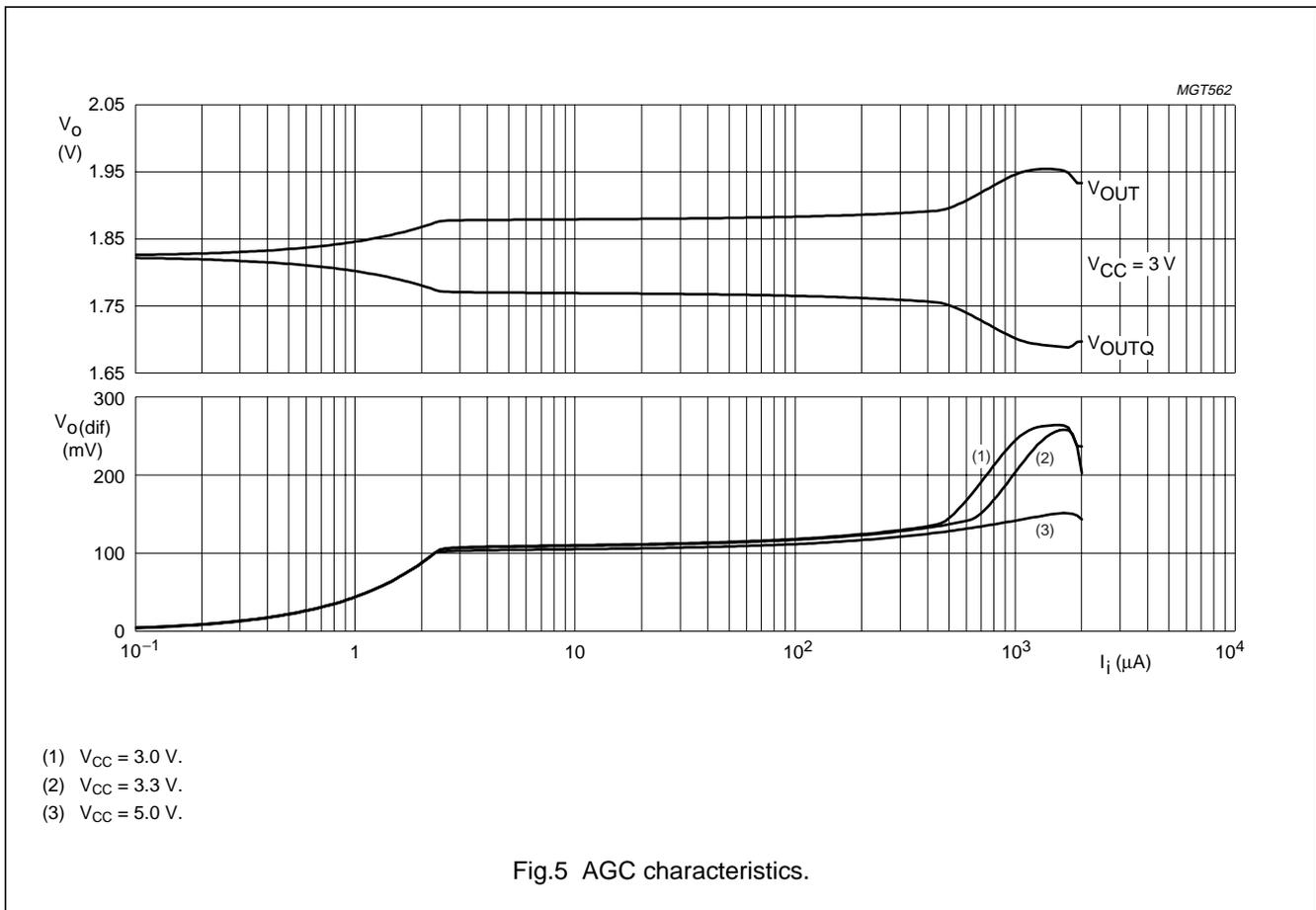
AGC

The TZA3033 transimpedance amplifier can handle input currents from 0.25 μA to 1.6 mA. This means a dynamic range of 79 dB. At low input currents, the transimpedance must be high to obtain an adequate output voltage, and the noise should be suitably low to guarantee minimum bit error rate. At high input currents however, the transimpedance should be low to avoid pulse width distortion. This means that the gain of the amplifier has to vary depending on the input signal level to handle such a wide dynamic range. This is achieved in the TZA3033 by implementing an Automatic Gain Control (AGC) loop.

The AGC loop consists of a peak detector, a hold capacitor and a gain control circuit. The peak amplitude of the signal is detected by the peak detector and stored on the hold capacitor. The voltage across the hold capacitor is compared to a threshold level. The threshold level is set at an input current of 2.5 μA (p-p). AGC becomes active only for input signals larger than the threshold level. It is disabled for smaller signals. The transimpedance is then at its maximum value (44 k Ω differential).

When the AGC is active, the feedback resistance of the transimpedance amplifier is reduced to keep the output voltage constant. The transimpedance is regulated from 44 k Ω at low currents ($I < 2.5 \mu\text{A}$) to 200 Ω at high currents ($I < 500 \mu\text{A}$). Above 500 μA the transimpedance is at its minimum and can not be reduced further but the front-end remains linear until input currents of 1.6 mA (p-p).

The upper graph of Fig.5 shows the output voltages V_{OUT} and V_{OUTQ} of the TZA3033 as a function of the DC input current for a supply voltage of 3 V. In the lower graph the difference between both output voltages, $V_{\text{O(dif)}}$, is shown for supply voltages of 3, 3.3 and 5 V. It can be seen from the graph that the output changes linearly up to an input current of 2.5 μA where the AGC becomes active. From this point on, the AGC tries to keep the differential output voltage constant around 110 mV for medium range input currents (input currents $< 200 \mu\text{A}$). The AGC can not regulate for input currents above 500 μA , and the output voltage rises again with the input current.



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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{CC}	supply voltage	-0.5	+5.5	V
V_n	DC voltage			
	pin 3/pad 5: IPhoto	-0.5	+2	V
	pins 6 and 7/pads 11 and 12: OUT and OUTQ	-0.5	$V_{CC} + 0.5$	V
	pad 15: AGC (TZA3033U only)	-0.5	$V_{CC} + 0.5$	V
	pin 1/pad 1: DREF	-0.5	$V_{CC} + 0.5$	V
I_n	DC current			
	pin 3/pad 5: IPhoto	-1	+2.5	mA
	pins 6 and 7/pads 11 and 12: OUT and OUTQ	-15	+15	mA
	pad 15: AGC (TZA3033U only)	-0.2	+0.2	mA
	pin 1/pad 1: DREF	-2.5	+2.5	mA
P_{tot}	total power dissipation	-	300	mW
T_{stg}	storage temperature	-65	+150	°C
T_j	junction temperature	-	150	°C
T_{amb}	ambient temperature	-40	+85	°C

HANDLING

Precautions should be taken to avoid damage through electrostatic discharge. This is particularly important during assembly and handling of the bare die. Additional safety can be obtained by bonding the V_{CC} and GND pads first, the remaining pads may then be bonded to their external connections in any order.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th(j-s)}$	thermal resistance from junction to solder point	160	K/W

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CHARACTERISTICS

For typical values $T_{amb} = 25\text{ °C}$ and $V_{CC} = 5\text{ V}$; minimum and maximum values are valid over the entire ambient temperature range and process spread; all voltages are measured with respect to ground; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CC}	supply voltage		3	5	5.5	V
I_{CC}	supply current	AC coupled; $R_L = 50\ \Omega$ $V_{CC} = 5\text{ V}$	20	38	60	mA
		$V_{CC} = 3.3\text{ V}$	20	35	50	mA
P_{tot}	total power dissipation	$V_{CC} = 5\text{ V}$	100	190	330	mW
		$V_{CC} = 3.3\text{ V}$	60	116	180	mW
T_j	junction temperature		-40	-	+125	°C
T_{amb}	ambient temperature		-40	+25	+85	°C
R_{tr}	small-signal transresistance of the receiver	AC coupled; measured differentially $R_L = \infty$	42	90	112	k Ω
		$R_L = 50\ \Omega$	21	45	66	k Ω
$f_{-3dB(h)}$	high frequency -3 dB point	AC coupled; measured differentially; $C_i = 0.7\text{ pF}$; $R_L = 50\ \Omega$ $T_j = 125\text{ °C}$	90	130	-	MHz
		$T_j = 100\text{ °C}$	100	130	-	MHz
PSRR	power supply rejection ratio	measured differentially; note 1 $f = 100\text{ kHz to }10\text{ MHz}$	-	0.5	-	$\mu\text{A/V}$
		$f = 100\text{ MHz}$	-	10	-	$\mu\text{A/V}$
Bias voltage: pin DREF						
R_{DREF}	resistance between pins DREF and V_{CC}	DC tested	210	245	290	Ω
Input: pin IPhoto						
$V_{bias(IPhoto)}$	input bias voltage on pin IPhoto		800	1050	1300	mV
$I_{i(IPhoto)(p-p)}$	input current on pin IPhoto (peak-to-peak value)	note 2 $V_{CC} = 5\text{ V}$	0	1	1800	μA
		$V_{CC} = 3.3\text{ V}$	0	1	1600	μA
R_i	small-signal input resistance	$f_i = 1\text{ MHz}$; input current $< 0.5\ \mu\text{A}$	-	330	-	Ω
$I_{n(tot)}$	total integrated RMS noise current over bandwidth (referenced to input)	$\Delta f = 90\text{ MHz}$; note 3	-	16	-	nA

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Data outputs: OUT and OUTQ						
$V_{o(cm)}$	common mode output voltage	AC coupled; $R_L = 50 \Omega$	$V_{CC} - 1.34$	$V_{CC} - 1.15$	$V_{CC} - 0.96$	V
$V_{o(se)(p-p)}$	single-ended output voltage (peak-to-peak value)	AC coupled; $R_L = 50 \Omega$; input current = $100 \mu A_{(p-p)}$	40	110	200	mV
V_{OO}	differential output offset voltage	$V_{CC} = 5 V$	-50	+55	+150	mV
		$V_{CC} = 3.3 V$	-50	+35	+100	mV
$R_{o(se)}$	single-ended output resistance	DC tested	36	44	57	Ω
t_r	rise time	20% to 80%	–	2.3	3.9	ns
t_f	fall time	80% to 20%	–	2.3	3.9	ns
Automatic gain control loop: pad AGC						
$I_{th(AGC)}$	AGC threshold current	referred to the peak input current; tested at 10 MHz	–	2.5	–	μA
$t_{att(AGC)}$	AGC attack time		–	5	–	μs
$t_{decay(AGC)}$	AGC decay time		–	10	–	ms

Notes

1. PSRR is defined as the ratio of the equivalent current change at the input (ΔI_{Photo}) to a change in supply voltage:

$$PSRR = \frac{\Delta I_{Photo}}{\Delta V_{CC}}$$

For example, a + 4 mV disturbance on V_{CC} at 10 MHz will typically add an extra 2 nA to the photodiode current. The external capacitor between DREF and GND has a large impact on PSRR. The specification is valid with an external capacitor of 1 nF. The PSRR is guaranteed by design.

2. The Pulse Width Distortion (PWD) is <5% over the whole input current range. The PWD is defined as:

$$PWD = \left(\frac{\text{pulse width}}{T} - 1 \right) \times 100\% \quad \text{where } T \text{ is the clock period. The PWD is measured differentially with}$$

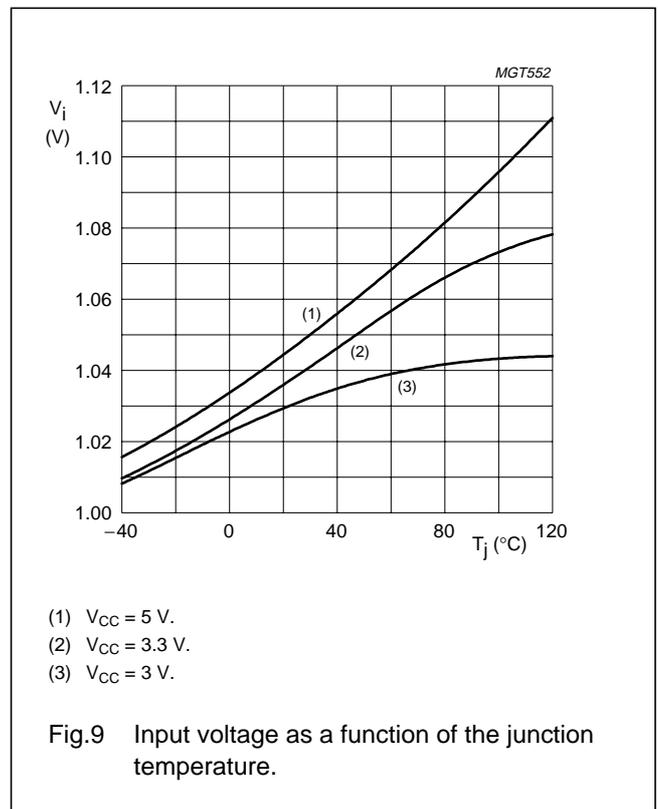
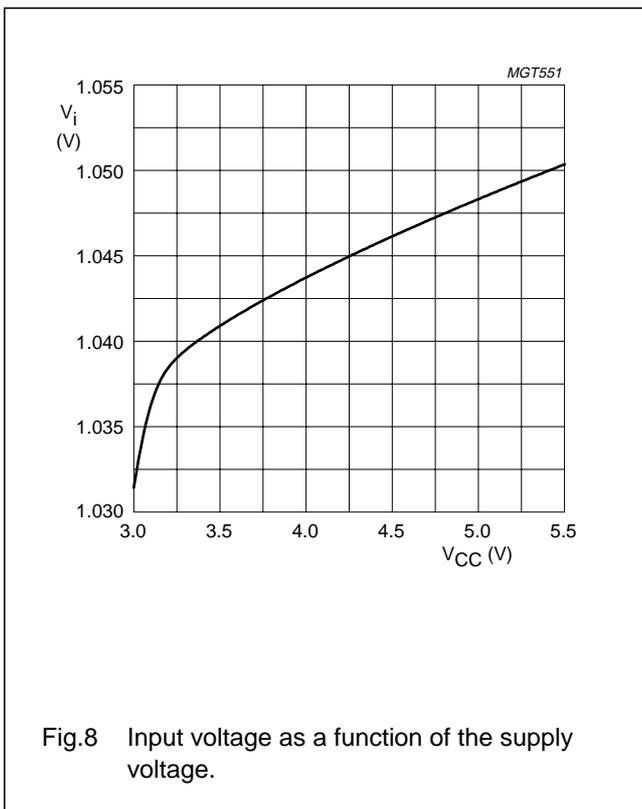
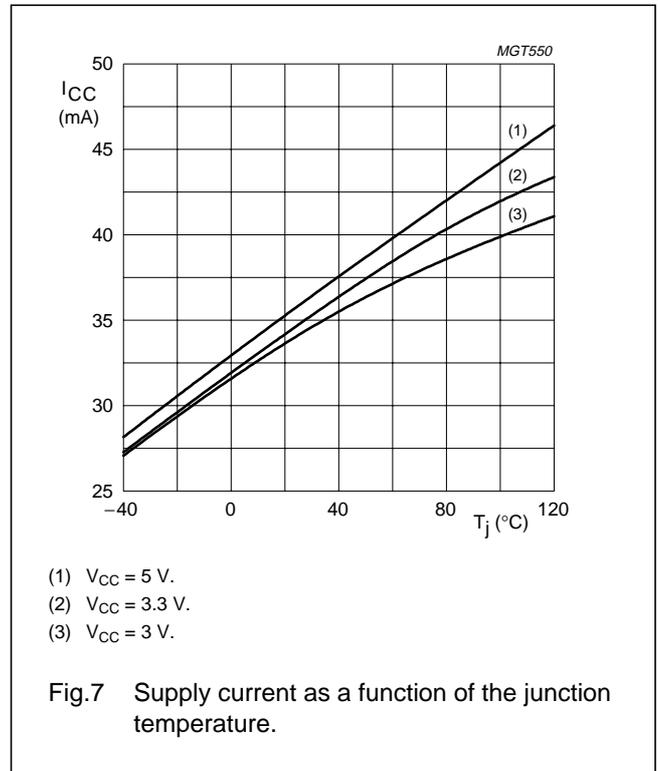
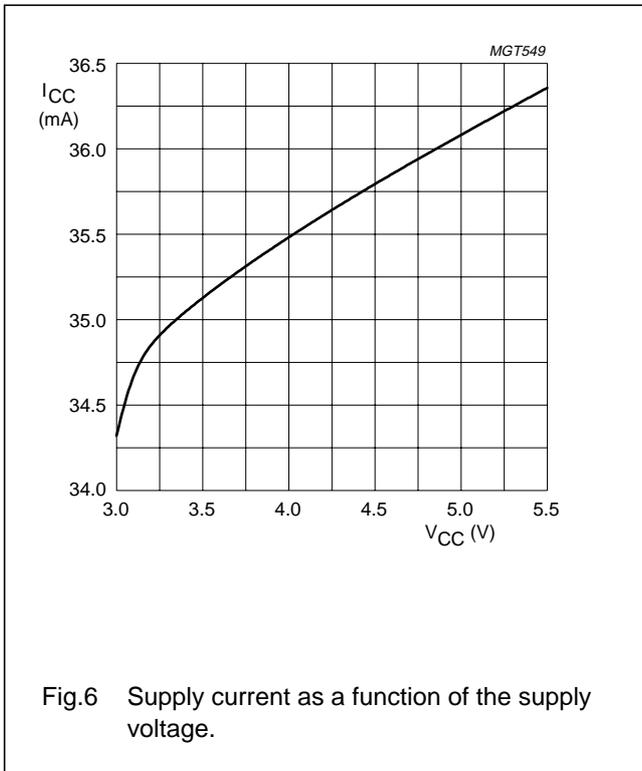
PRBS pattern of 10^{-23} .

3. All $I_{n(tot)}$ measurements were made with an input capacitance of $C_i = 1 \text{ pF}$. This was comprised of 0.5 pF for the photodiode itself, with 0.3 pF allowed for the printed-circuit board layout and 0.2 pF intrinsic to the package. Noise performance is measured differentially.

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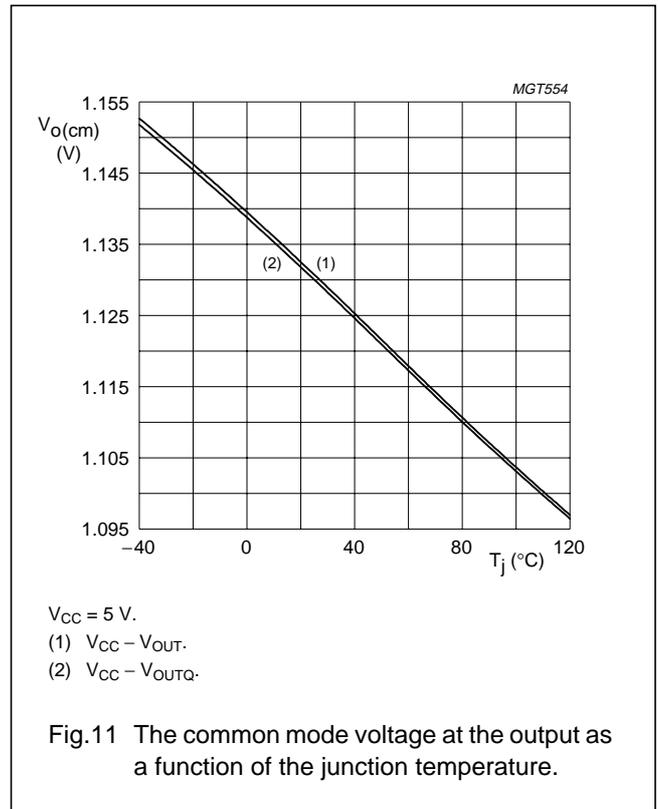
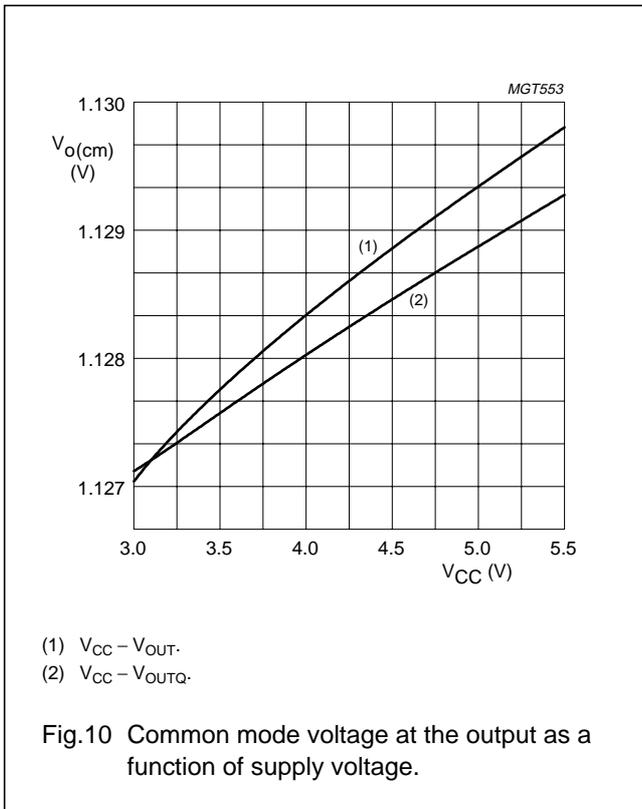
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TYPICAL PERFORMANCE CHARACTERISTICS

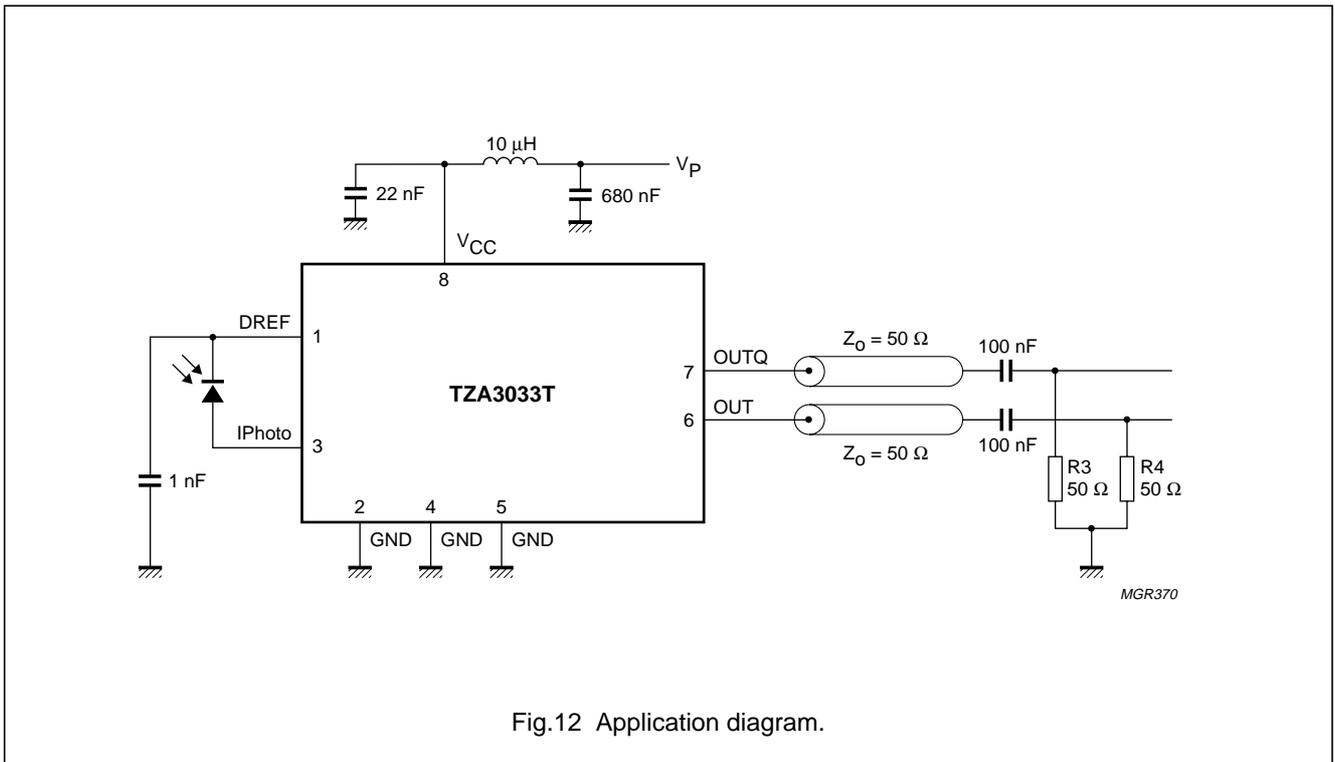


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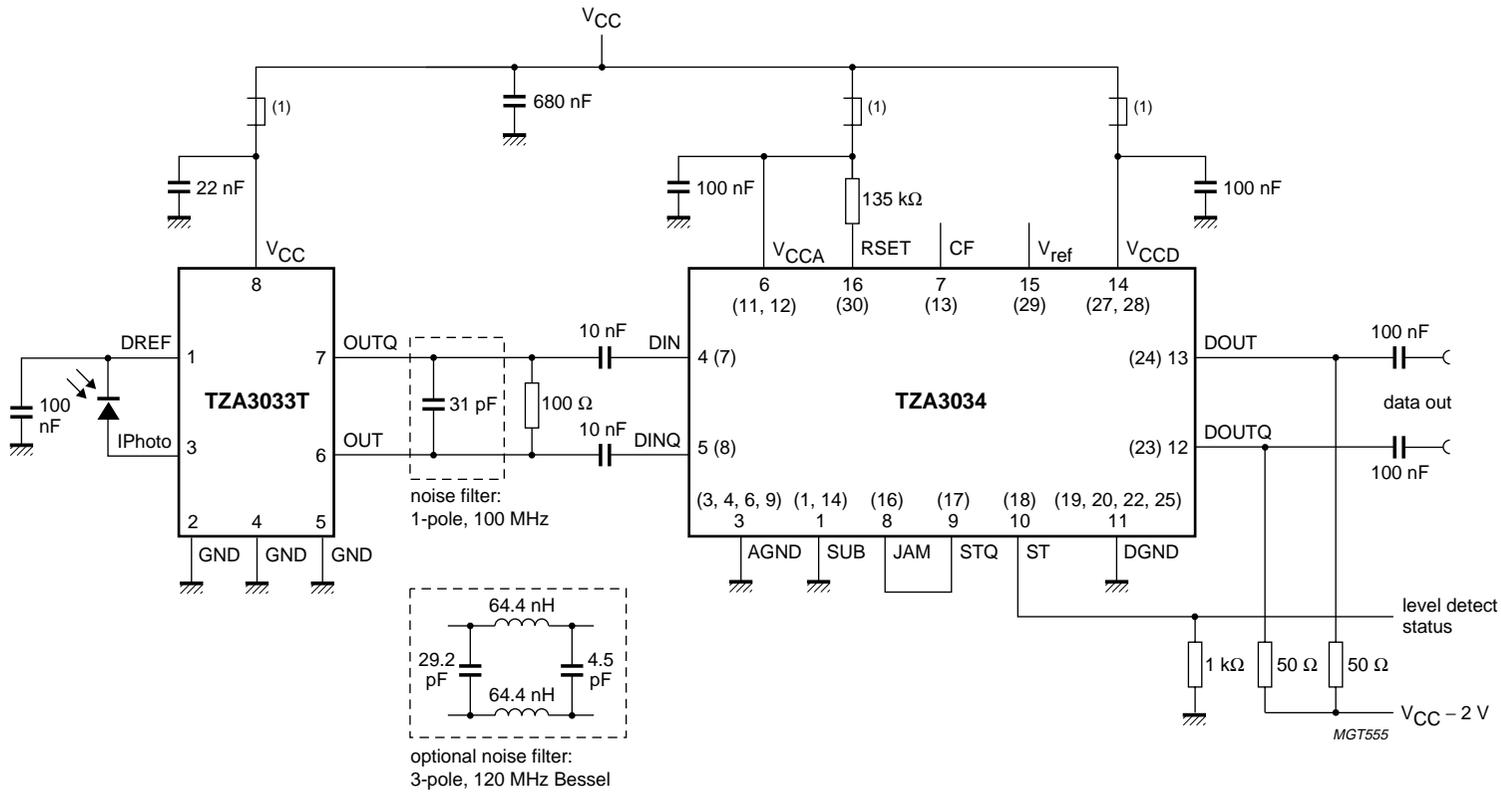


APPLICATION INFORMATION



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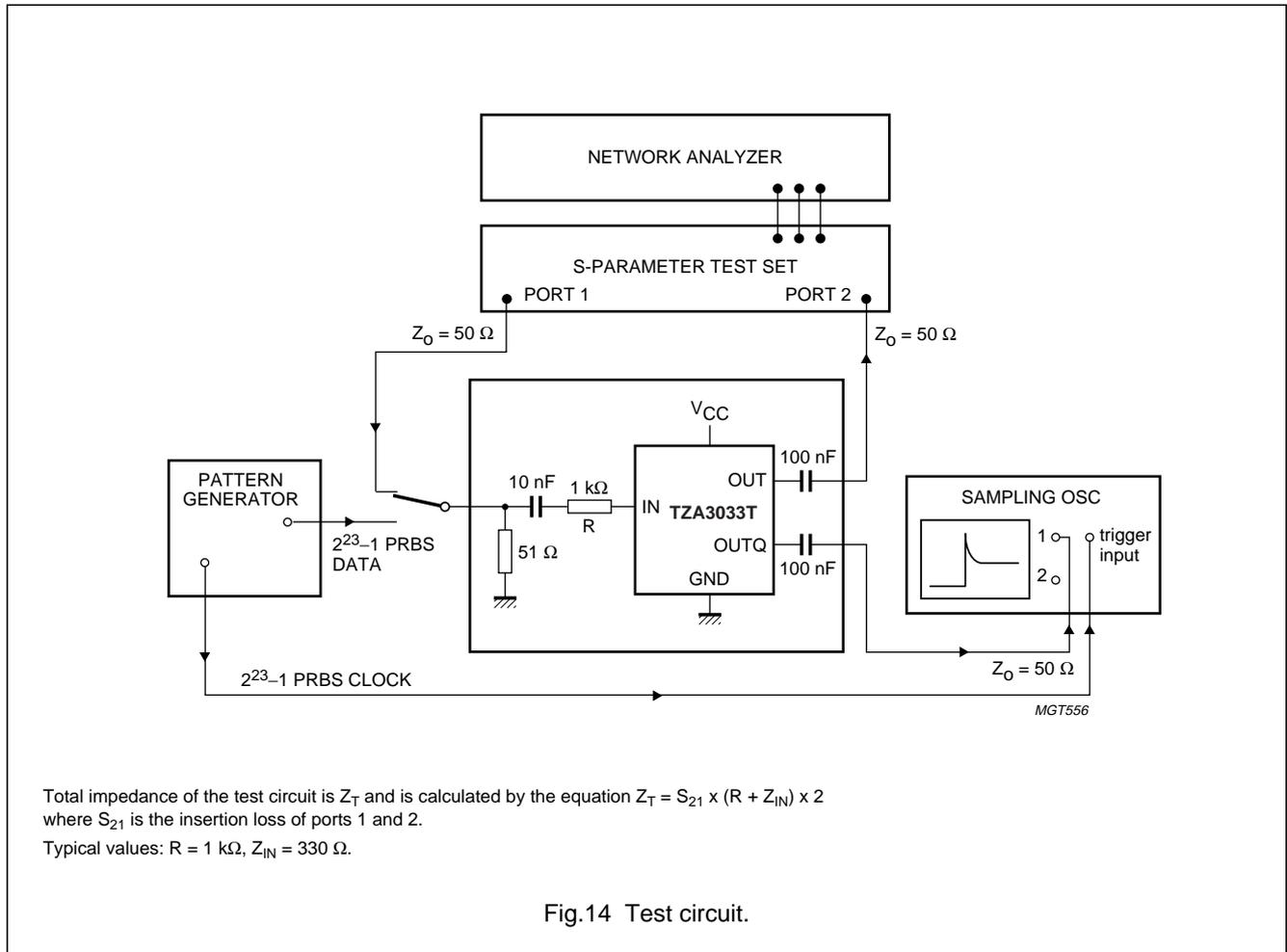
(1) Ferrite bead e.g. Murata BLM10A700S.

Fig.13 STM1/OC3 receiver using the TZA3033 and TZA3034.

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Test circuits



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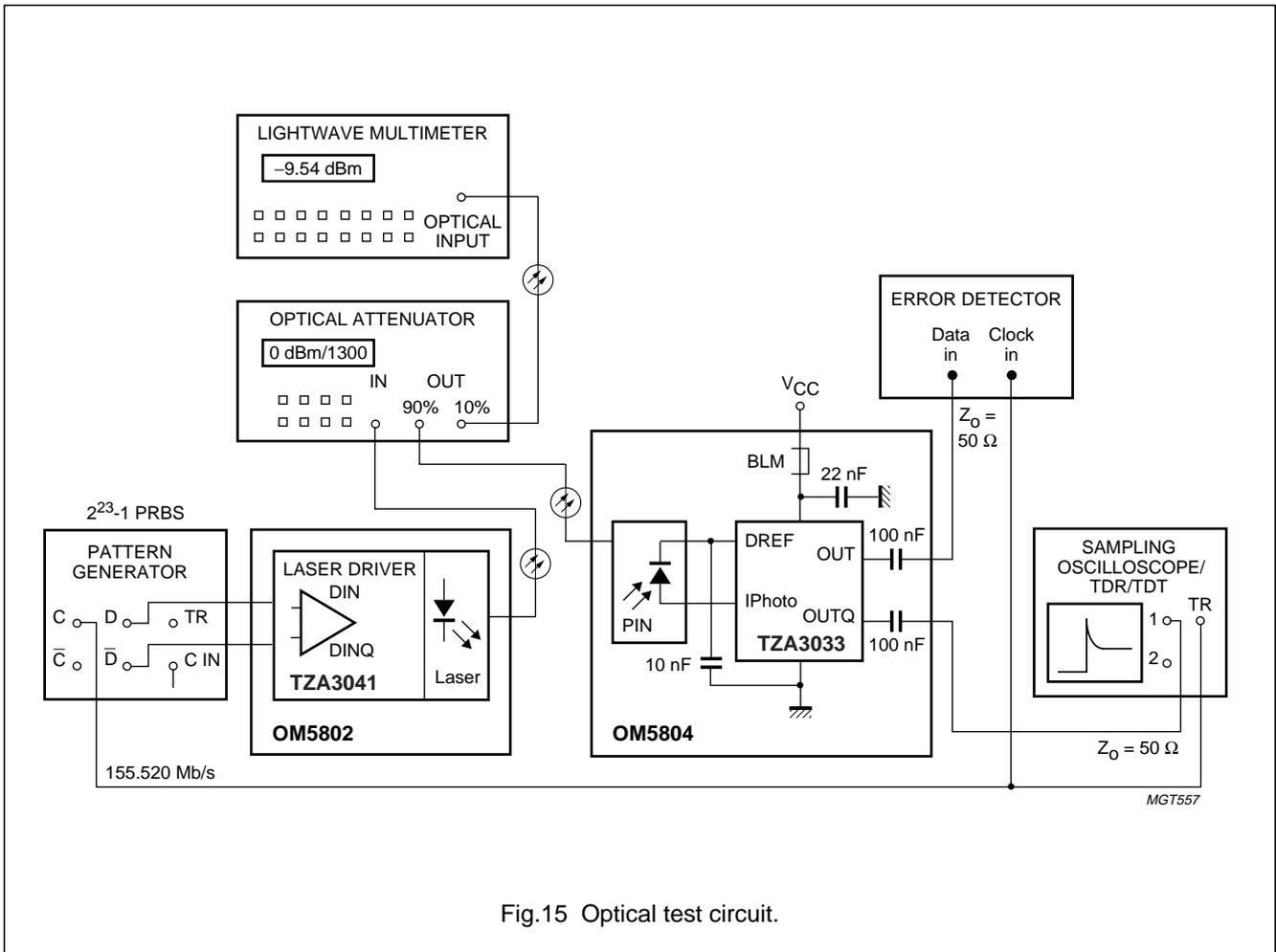


Fig.15 Optical test circuit.

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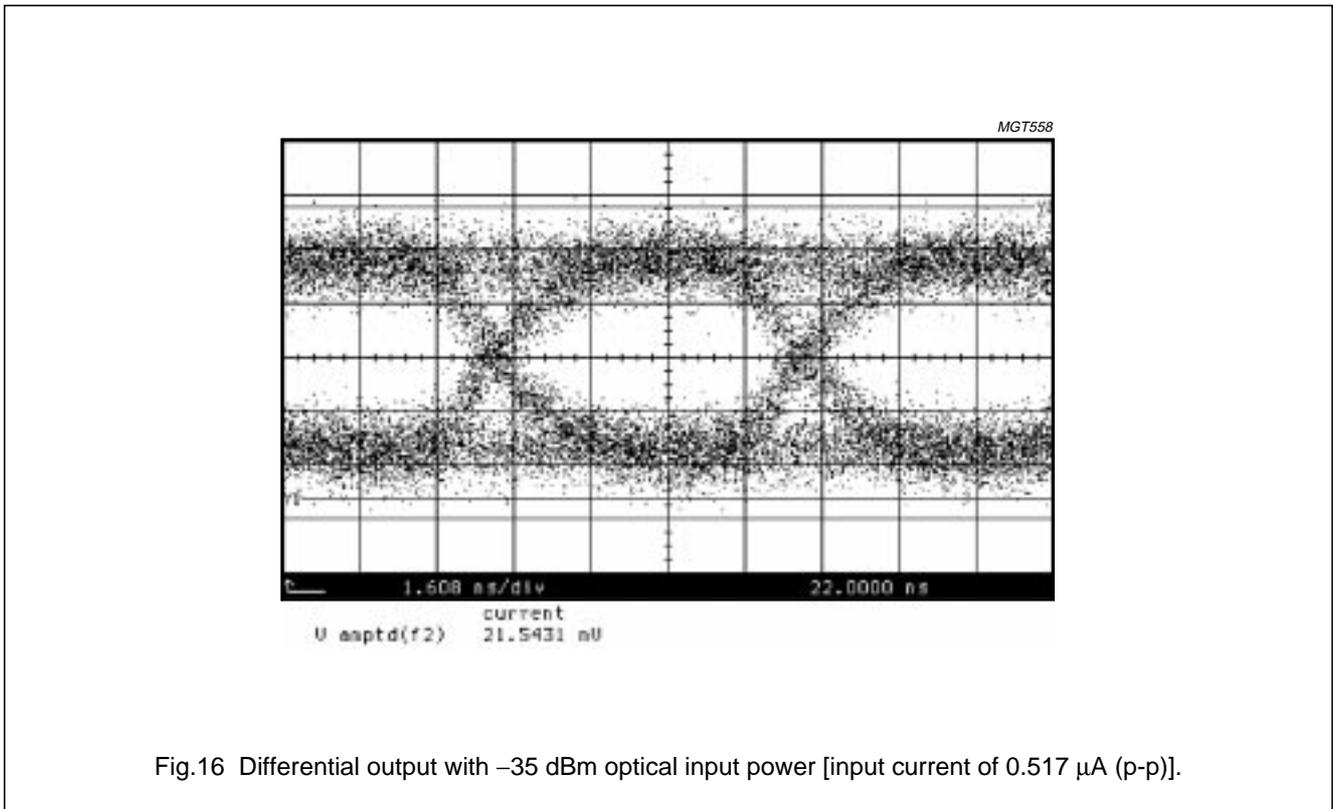


Fig.16 Differential output with -35 dBm optical input power [input current of 0.517 μ A (p-p)].

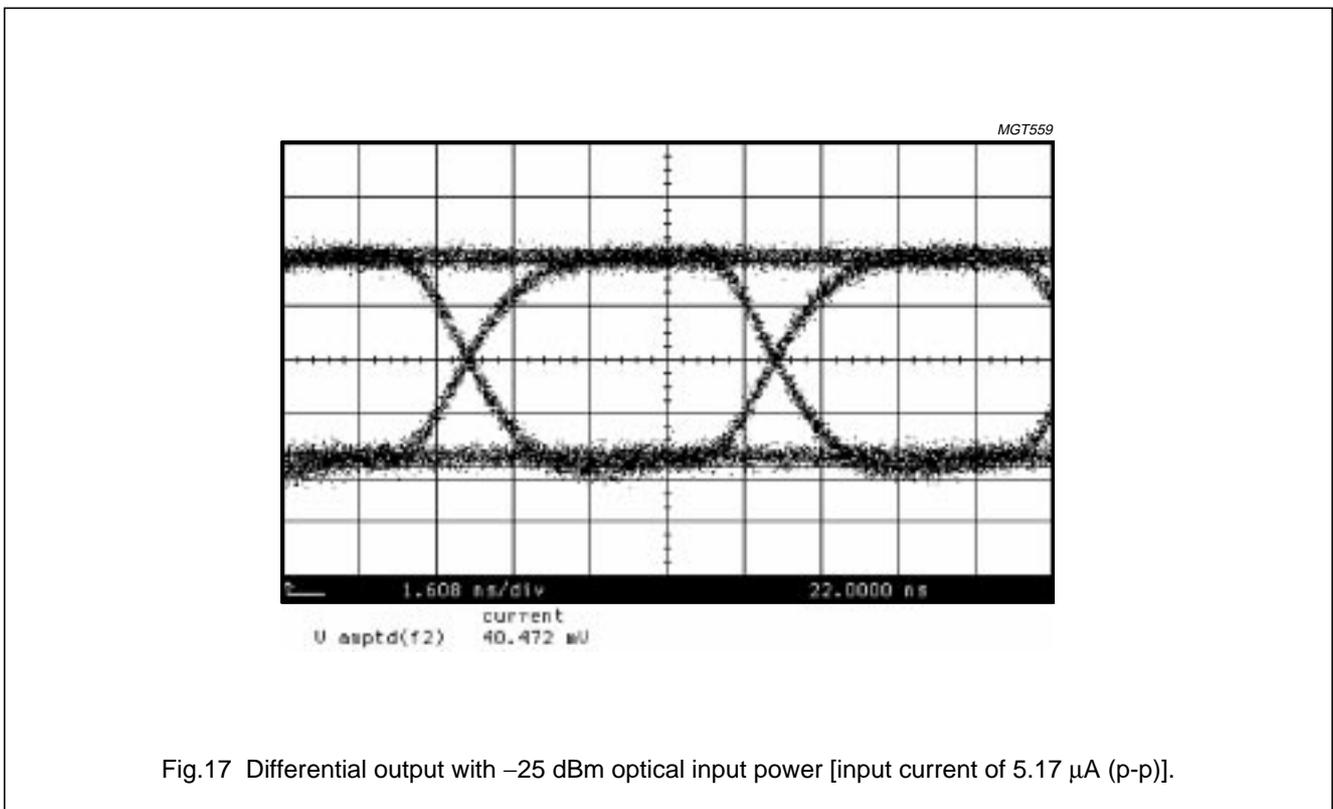
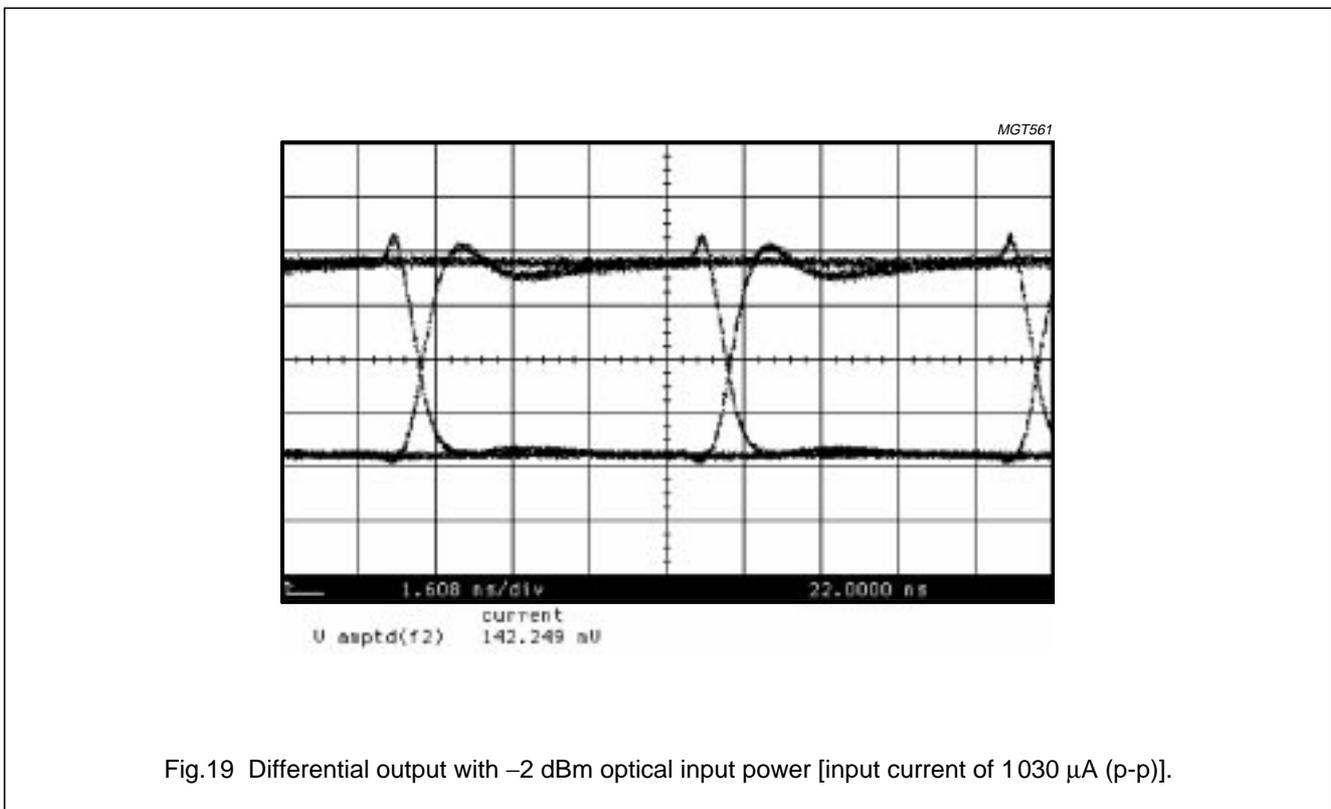
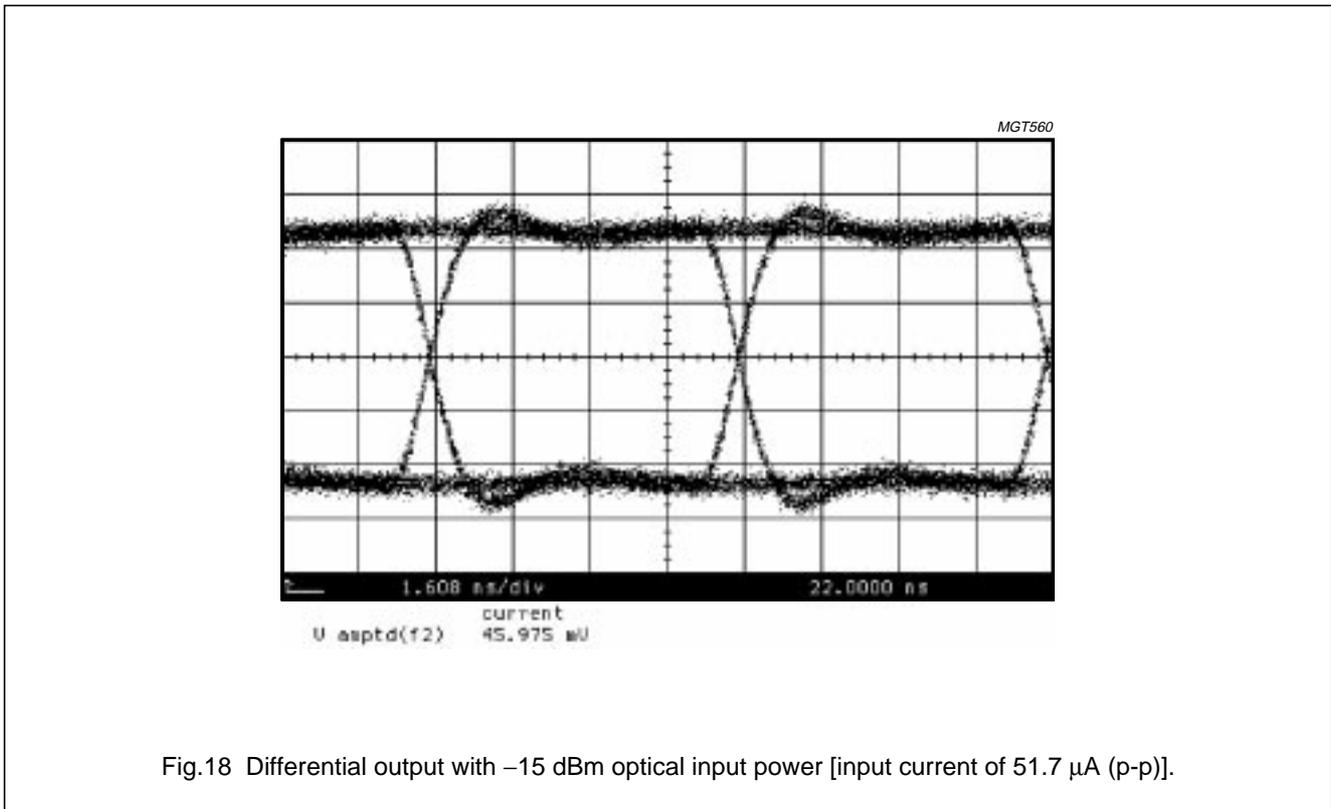


Fig.17 Differential output with -25 dBm optical input power [input current of 5.17 μ A (p-p)].

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BONDING PAD LOCATIONS

SYMBOL	PAD	COORDINATES ⁽¹⁾	
		x	y
DREF	1	95	881
TESTA	2	95	735
GND	3	95	618
GND	4	95	473
IPhoto	5	95	285
TESTB	6	95	147
GND	7	215	95
GND	8	360	95
GND	9	549	95
GND	10	691	95
OUT	11	785	501
OUTQ	12	785	641
V _{CC}	13	567	1055
V _{CC}	14	424	1055
AGC	15	259	1055

Note

1. All coordinates are referenced, in μm , to the bottom left-hand corner of the die.

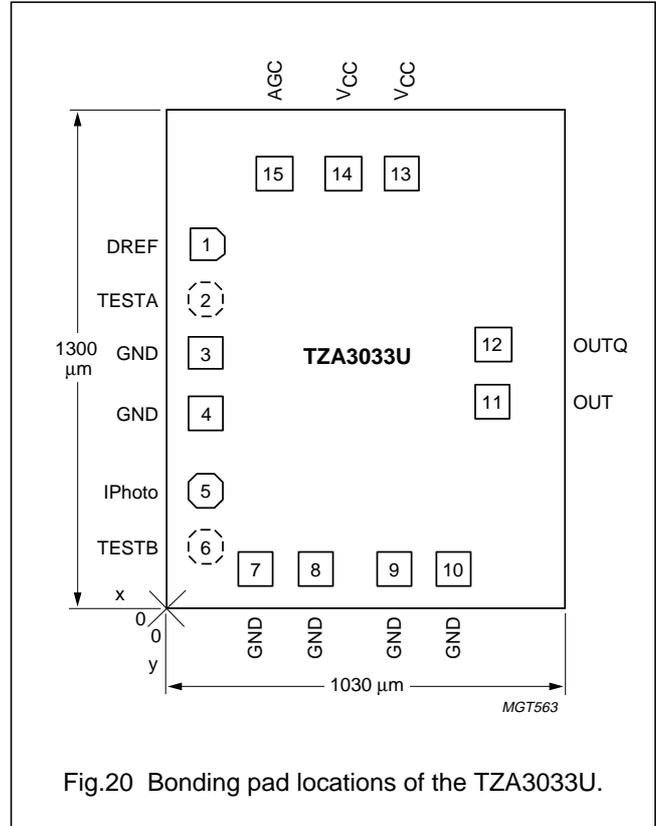


Fig.20 Bonding pad locations of the TZA3033U.

Physical characteristics of the bare die

PARAMETER	VALUE
Glass passivation	2.1 μm PhosphoSilicate Glass (PSG) on top of 0.65 μm oxynitride
Bonding pad dimension	minimum dimension of exposed metallization is $90 \times 90 \mu\text{m}$ (pad size = $100 \times 100 \mu\text{m}$)
Metallization	1.22 μm W/AICu/TiW
Thickness	380 μm nominal
Size	$1.03 \times 1.30 \text{ mm}$ (1.34 mm^2)
Backing	silicon; electrically connected to GND potential through substrate contacts
Attach temperature	<440 °C; recommended die attach is glue
Attach time	<15 s

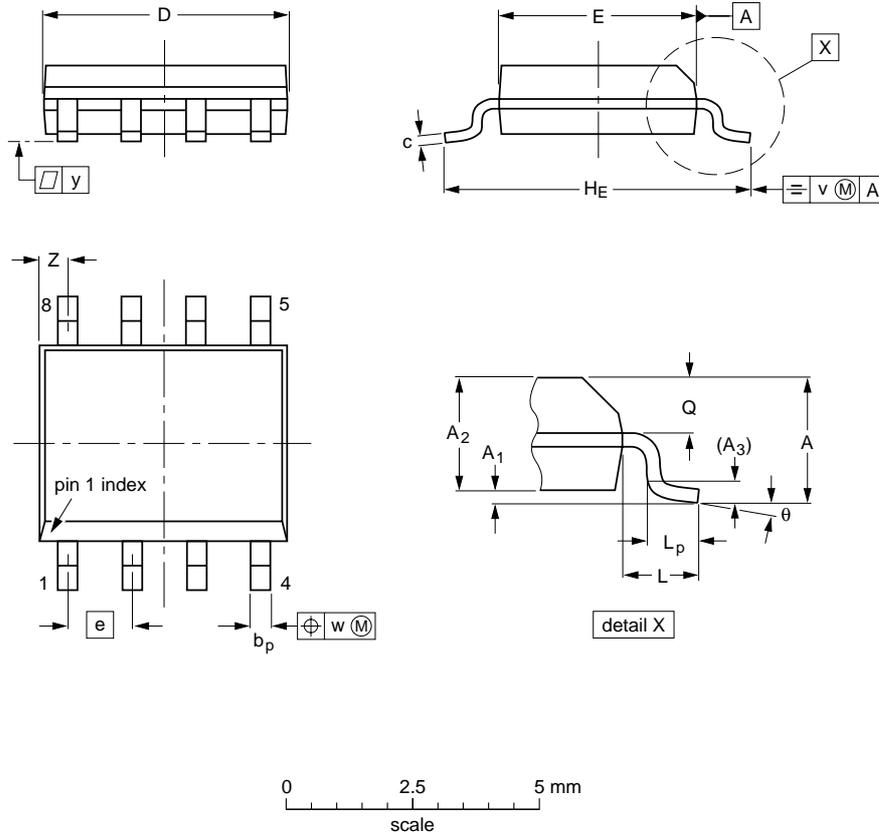
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PACKAGE OUTLINE

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.20 0.19	0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT96-1	076E03	MS-012				97-05-22 99-12-27

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SOLDERING**Introduction to soldering surface mount packages**

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferably be kept below 220 °C for thick/large packages, and below 235 °C for small/thin packages.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

- For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

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Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD	
	WAVE	REFLOW ⁽¹⁾
BGA, LFBGA, SQFP, TFBGA	not suitable	suitable
HBCC, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, SMS	not suitable ⁽²⁾	suitable
PLCC ⁽³⁾ , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended ⁽³⁾⁽⁴⁾	suitable
SSOP, TSSOP, VSO	not recommended ⁽⁵⁾	suitable

Notes

1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

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DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS ⁽¹⁾
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

Note

1. Please consult the most recently issued data sheet before initiating or completing a design.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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NOTES

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NOTES

Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 3 Figtree Drive, HOMEBUSH, NSW 2140,
Tel. +61 2 9704 8141, Fax. +61 2 9704 8139

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,
Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

Belgium: see The Netherlands

Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 68 9211, Fax. +359 2 68 9102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Sydhavnsgade 23, 1780 COPENHAGEN V,
Tel. +45 33 29 3333, Fax. +45 33 29 3905

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615 800, Fax. +358 9 6158 0920

France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex,
Tel. +33 1 4099 6161, Fax. +33 1 4099 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 2353 60, Fax. +49 40 2353 6300

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor,
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,
Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: PT Philips Development Corporation, Semiconductors Division,
Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,
Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Via Casati, 23 - 20052 MONZA (MI),
Tel. +39 039 203 6838, Fax +39 039 203 6800

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,
TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5057

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Pakistan: see Singapore

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Al.Jerozolimskie 195 B, 02-222 WARSAW,
Tel. +48 22 5710 000, Fax. +48 22 5710 001

Portugal: see Spain

Romania: see Italy

Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 319762,
Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria

Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 58088 Newville 2114,
Tel. +27 11 471 5401, Fax. +27 11 471 5398

South America: Al. Vicente Pinzon, 173, 6th floor,
04547-130 SÃO PAULO, SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 821 2382

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 93 301 6312, Fax. +34 93 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
Tel. +46 8 5985 2000, Fax. +46 8 5985 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,
Tel. +41 1 488 2741 Fax. +41 1 488 3263

Taiwan: Philips Semiconductors, 5F, No. 96, Chien Kuo N. Rd., Sec. 1,
TAIPEI, Taiwan Tel. +886 2 2134 2451, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
60/14 MOO 11, Bangna Trad Road KM. 3, Bagna, BANGKOK 10260,
Tel. +66 2 361 7910, Fax. +66 2 398 3447

Turkey: Yukari Dudullu, Org. San. Blg., 2.Cad. Nr. 28 81260 Umraniye,
ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 208 730 5000, Fax. +44 208 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,
Tel. +381 11 3341 299, Fax.+381 11 3342 553

For all other countries apply to: Philips Semiconductors,
Marketing Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN,
The Netherlands, Fax. +31 40 27 24825

Internet: <http://www.semiconductors.philips.com>

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